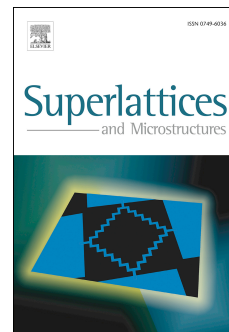


Accepted Manuscript

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PII: S0749-6036(18)30366-5

DOI: [10.1016/j.spmi.2018.04.024](https://doi.org/10.1016/j.spmi.2018.04.024)

Reference: YSPMI 5638

To appear in: *Superlattices and Microstructures*

Received Date: 23 February 2018

Revised Date: 7 April 2018

Accepted Date: 9 April 2018

Please cite this article as: A. Ariff, M.A. Ahmad, Z. Hassan, N. Zainal, Influence of ammonia flow rate for improving properties of polycrystalline GaN, *Superlattices and Microstructures* (2018), doi: 10.1016/j.spmi.2018.04.024.

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Influence of ammonia flow rate for improving properties of polycrystalline GaN

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Abstract

Post-annealing treatment in ammonia ambient is widely accepted for GaN material, but less works have been done to investigate the influence of the ammonia (NH₃) flow rate for reducing the N-deficiency as well as improving the quality of the material. In this work, we investigated the influence of NH₃ flow rate at 1, 2, 3, and 4 slm in improving properties of a ~1 μm thick polycrystalline GaN layer. Our simulation work suggested that the uniformity of temperature and pressure gradient of the NH₃ gas did not lead to the reduction of N-deficiency of the polycrystalline GaN layer. Instead, it was found that the mitigation of the N-deficiency was strongly influenced by the fluid velocity of the NH₃ gas, which had passed over the layer. Either at lower or higher fluid velocity, the chance for the active N atoms to incorporate into the GaN lattice structure was low. Therefore, the N-deficiency on the polycrystalline GaN layer could not be minimized under these conditions. As measured by EDX, the N atoms incorporation was the most effective when the NH₃ flow rate at 3 slm, suggesting the flow rate significantly improved the N-deficiency of the polycrystalline GaN layer. Furthermore, it favored the formation of larger hexagonal faceted grains, with the smallest FWHM of XRD peaks from the GaN diffractions in (10 $\bar{1}$ 0), (0002) and (10 $\bar{1}$ 1) orientations, while allowing the polycrystalline GaN layer to show sharp and intense emissions peak of NBE in a PL spectrum.

Keywords: Polycrystalline GaN; ammonia annealing; ammonia flow rate; N-deficiency

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